

| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|-------|--|--|------------------|---------|------------------|
| L2 | 106 | ((LTPS adj TFT) or (low adj temperature adj polycrystalline adj silicon adj thin adj film adj transistor)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 21:21 |
| L3 | 10057 | ((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/406) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/12/08 21:21 |
| L4 | 103 | 2 and "1" | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 21:26 |
| L5 | 21 | 2 and 3 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 21:22 |
| L6 | 75 | 2 and (amorphous) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 22:30 |
| L7 | 19 | 6 and 3 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 21:26 |
| L8 | 42860 | (spc or (solid adj phas adj crystallization)) or (milc or (metal adj induced adj lateral adj crystallization)) or (ela or (excimer adj laser adj annealing)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 22:33 |

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|-----|-------|---|---|----|-----|------------------|
| L9 | 27 | 8 and 2 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 22:33 |
| L10 | 0 | ("2004/0217424").URPN. | USPAT | OR | OFF | 2004/12/08 22:38 |
| L11 | 1 | ("6242292").PN. | USPAT | OR | OFF | 2004/12/08 22:38 |
| L12 | 52 | ("3848104" "4046618" "4059461" "4083272" "4160263" "4234358" "4249960" "4266986" "4309225" "4328553" "4341569" "4370175" "4439245" "4463028" "4468551" "4469551" "4545823" "4734550" "4764485" "4803528" "4835704" "4862227" "4937618" "4942058" "4956539" "4970366" "5217921" "5219786" "5221365" "5247375" "5313076" "5352291" "5365875" "5372836" "5413958" "5424230" "5424244" "5432122" "5477073" "5561081" "5572046" "5578520" "5589406" "5612251" "5622814" "5648277" "5696003" "5708252" "5712191" "5736414" "5756364" "5858473").PN. | US-PGPUB; USPAT; USOCR | OR | OFF | 2004/12/08 22:40 |
| L14 | 20 | ((("5365080") or ("5847419") or ("6607948") or ("6674100") or ("5063166") or ("4962051") or ("4962051") or ("4914053") or ("4868614")).PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/12/08 23:10 |
| L15 | 2 | ("5818053").PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/12/08 23:10 |
| S1 | 10057 | ((438/149) or (438/151) or (438/164) or (438/166) or (438/311) or (438/412) or (438/378) or (438/479) or (438/482) or (438/486) or (438/487) or (438/488) or (438/489) or (438/490) or (438/595) or (438/596) or (438/704) or (438/406) or (438/735) or (438/745) or (438/764) or (438/795) or (438/800) or (438/902)).CCLS. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/12/08 21:21 |

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| S2 | 12 | (("4330363") or ("4592799") or ("5021119") or ("5395481") or ("6495405")).PN. | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2004/12/08 23:06 |
| S3 | 2901 | ((polycrystalline near2 silicon) or (poly adj silicon)) near2 (tft or ((thin near2 film) near2 transistor\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:34 |
| S4 | 1053 | ((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or (sidewall near2 spacer\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 21:19 |
| S5 | 8 | S3 and S4 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:36 |
| S6 | 1 | S1 and S5 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:36 |
| S7 | 1152 | ((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 18:04 |
| S8 | 4082 | S7 and3 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:39 |
| S9 | 12 | S7 and S3 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:39 |

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| S10 | 1 | S9 and S1 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:39 |
| S11 | 11 | S9 not S10 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:40 |
| S12 | 16 | ((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or (sidewall near2 spacer\$1)) same (active near2 (layer\$1 or film\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:44 |
| S13 | 16 | ((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or.(capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1)) same (active near2 (layer\$1 or film\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:54 |
| S14 | 6 | ((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1)) near10 (active near2 (layer\$1 or film\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:52 |
| S15 | 10 | S13 not S14 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:52 |
| S16 | 0 | ("2004/0026738").URPN. | USPAT | OR | OFF | 2004/12/08 17:53 |
| S17 | 123 | ((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1))and (active near2 (layer\$1 or film\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:55 |
| S18 | 107 | S17 not S13 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 17:55 |

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| S19 | 33 | ((polycrystalline near2 silicon) or (poly adj silicon)) near3 (spacer\$1 or sidewall\$1 or capp\$3 or (capp\$3 near2 (layer or film)) or (sidewall near2 spacer\$1)) same (crystall\$7 or recrystall\$7) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 18:05 |
| S20 | 7 | S19 and (active near2 (layer\$1 or film\$1)) | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 18:07 |
| S21 | 0 | S19 not S7 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 18:08 |
| S22 | 26 | S19 not S20 | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2004/12/08 18:09 |